

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

10010482

SERIAL NO.

APPLICANT

Frank H. Peters et al.

FILING DATE

12/31/2001

GROUP

10/04/01
12/31/01
10/04/01
12/31/01

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME
	1A			
	1B			
	1C			
	1D			
	1E			
	1F			
	1G			
	1H			
	1I			
	1J			
	1K			

#3
31 May 02
R. Tallor

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	TRANSLATION	
					YES	NO
	1L					
	1M					
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

1Q	Boucarter, J. et al., "Implantation Optimization For 1.55 um VCSEL," 11th International Conference on Indium Phosphide and Related Materials, May 16-20, 1999, Davos, Switzerland, IEEE 0-7803-5562, pages 87-90 (August 1999).
1R	Ortsiefer, M. et al., "Room-temperature Operation of Index-guided 1.55 um InP-based Vertical-Cavity Surface-emitting Laser," Electronics Letters, Vol. 36, No. 5, pages 437-439 (March 2, 2000).
1S	Sekiguchi, S. et al., "Selectively Formed AlAs/InP Current Confining Tunnel Junction For GaInAsP/InP Surface Emitting Lasers," 11th International Conference on Indium Phosphide and Related Materials, May 16-20, 1999, Davos, Switzerland, IEEE 0-7803-5562, pages 211-214 (August 1999).

EXAMINER

DATE CONSIDERED

10-03

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME
	2A			
	2B			
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	2G			
	2H			
	2I			
	2J			
	2K			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	TRANSLATION	
					YES	NO
	2L					
	2M					
	2N					
	2O					
	2P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

	2Q	Sekiguchi, S. et al., "Long Wavelength GaInAsP/InP Laser With Automatically Formed Tunneling Aperture," IEEE 0-7803-6320 pages 451-454 (May 2000).
	2R	
	2S	

EXAMINER

DATE CONSIDERED

FORM PTO-1449

ATTY. DOCKET NO.

SERIAL NO.

10010482-1

10/040,167

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

APPLICANT

Frank H. Peters

FILING DATE

12/31/2001

GROUP

2811

(Use several sheets if necessary)

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	*	DOCUMENT NUMBER	DATE	NAME
gml		6,052,398	4/18/2000	Brillouet et al

FOREIGN PATENT DOCUMENTS

	*	DOCUMENT NUMBER	DATE	NAME	TRANSLATION	
					YES	NO
gml		WO 98/07218	2/19/1998	Gore		X
gml		JP2000277853	06/10/2000	Tokyo Institute (abstract only)	X	
gml		WO02/45223	6/6/2002	Optowell Co.		X
gml		DE19954343	5/23/2001	Infineon (abstract only)	X	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

gml	*	Indium Phosphide and Related Materials, 1999. IPRM. 1999 11th International Conference on 16-20 May 1999, IEEE, pp 211-214, S.Sekiguchi et al. "Selectively formed AlAs/InP current confining tunnel junction for GaInAsP/InP surface emitting lasers".
EXAMINER	DATE CONSIDERED	
gml	10/03	

* Copies of these references are not enclosed pursuant to 37 CFR 1.98(d). (See accompanying IDS)